

N-Ch MOSFET

General Description

The WST2N7002K is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent R_{DSON} and gate charge for most of the small power switching and load switch applications.

The WST2N7002K meet the RoHS and Green Product requirement with full function reliability approved.

Features

- High-speed switching
- Green Device Available
- ESD Protected:2KV

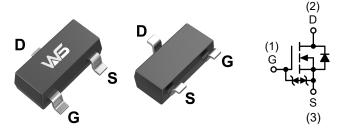
Product Summery

BV _{DSS}		I _D
60V	1000mΩ	0.3A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC
- Networking DC-DC Power System
- Load Switch

SOT-23L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	60	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D @T _A =25℃	Continuous Drain Current, V _{GS} @ 10V ¹	0.3	A	
I _D @T _A =70℃	Continuous Drain Current, V _{GS} @ 10V ¹	0.15	A	
I _{DM}	Pulsed Drain Current ²	1.2	A	
P _D @T _A =25℃	Total Power Dissipation ³	0.2	W	
T _{STG}	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{eja}	Thermal Resistance Junction-Ambient ¹		625	°C/W



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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V , I_{D} =250 uA	60			V	
$\triangle BV_{DSS} / \triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to $25^\circ\!\!\mathbb{C}$, I _D =1mA		0.05		V/℃	
B	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =0.5A		1000	3000	mΩ	
R _{DS(ON)}		V _{GS} =4.5V , I _D =0.2A		4000	5000		
V _{GS(th)}	Gate Threshold Voltage	Gate Threshold Voltage V _{GS(th)} Temperature Coefficient			2.5	V	
	V _{GS(th)} Temperature Coefficient			-3.7		mV/°C	
	Drain-Source Leakage Current	V_{DS} =60V , V_{GS} =0V , T_{J} =25 $^{\circ}$ C			1	uA	
I _{DSS}		V_{DS} =60V , V_{GS} =0V , T_{J} =55 $^{\circ}$ C			5	uA	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±10	uA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =0.3A		300		mS	
T _{d(on)}	Turn-On Delay Time			15	6		
Tr	Rise Time	V_{DD} =30V , V_{GS} =10V , R_G =3.3 Ω ,		35	3.3		
T _{d(off)}	Turn-Off Delay Time I _D =0.5A			35	16	– ns	
T _f	Fall Time			35	13.6]	
C _{iss}	Input Capacitance			32	56		
C _{oss}	Output Capacitance V _{DS} =25V , V _{GS} =0V , f=1MHz			7	17	pF	
C _{rss}	Reverse Transfer Capacitance			3	10.6		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
ls	Continuous Source Current ^{1,4}				0.3	А
I _{SM}	Pulsed Source Current ^{2,4}	V _G =V _D =0V , Force Current			1.2	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃			1	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%$ 3.The power dissipation is limited by 150 $^\circ\!C$ junction temperature.

4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



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Typical Characteristics

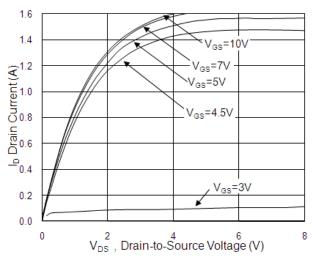


Fig.1 Typical Output Characteristics

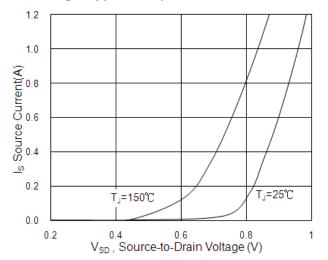


Fig.3 Forward Characteristics of Reverse

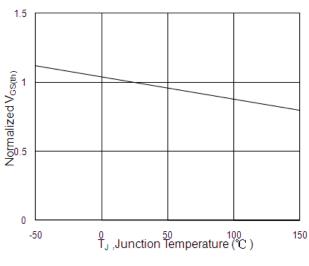
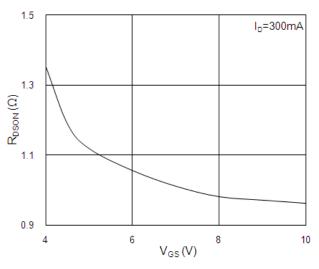
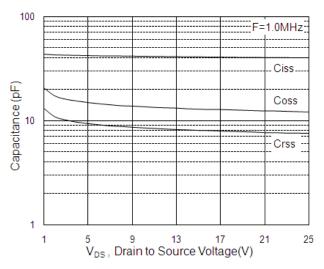


Fig.5 Normalized $V_{GS(th)}$ vs. T_J









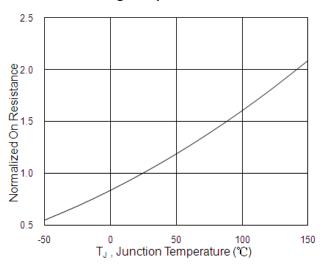


Fig.6 Normalized R_{DSON} vs. T_J



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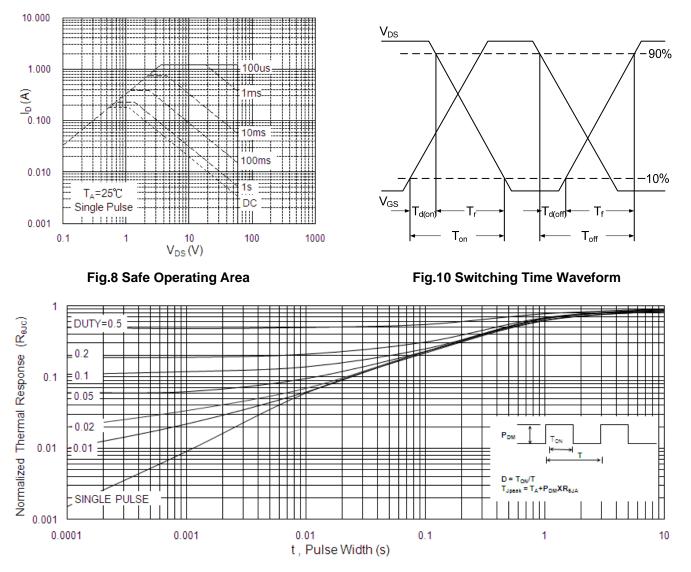
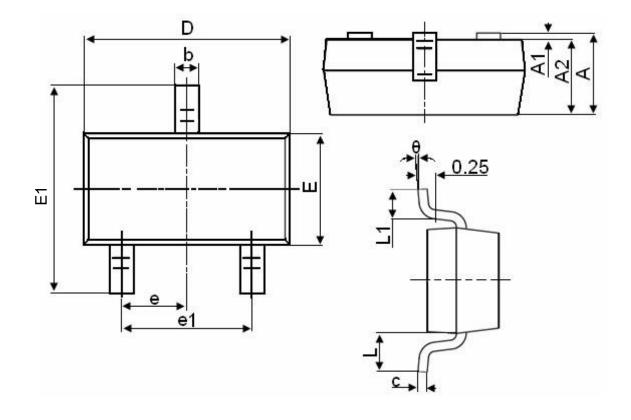


Fig.9 Normalized Maximum Transient Thermal Impedance



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Packaging information



Symbol	Dimensions in Millimeters			
Symbol	MIN.	MAX.		
A	0.900	1.150		
A1	0.000	0.100		
A2	0.900	1.050		
b	0.300	0.500		
С	0.080	0.150		
D	2.800	3.000		
E	1.200	1.400		
E1	2.250	2.550		
е	0.95	0.950TYP		
e1	1.800	2.000		
L	0.550REF			
L1	0.300	0.500		
θ	0°	8°		



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